



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

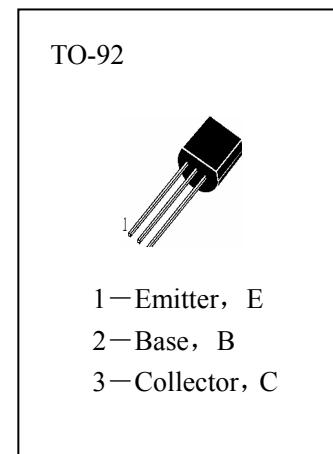
H1420

■ GENERAL PURPOSE AMPLIFIER AND LOW NOISE

AMPLIFIER APPLICATIONS

■ ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

T_{stg}	Storage Temperature	-55~150°C
T_j	Junction Temperature	150°C
P_c	Collector Dissipation	625mW
V_{CBO}	Collector-Base Voltage	60V
V_{CEO}	Collector-Emitter Voltage	60V
V_{EBO}	Emitter-Base Voltage	7V
I_c	Collector Current	200mA
I_B	Base Current	200mA



■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CEO}	Collector-Emitter Breakdown Voltage	60			V	$I_C=1\text{mA}, I_B=0$
I_{CBO}	Collector Cut-off Current			50	nA	$V_{CB}=40\text{V}, I_E=0$
I_{EBO}	Emitter Cut-off Current			100	nA	$V_{EB}=6\text{V}, I_C=0$
HFE	DC Current Gain	70		700		$V_{CE}=5\text{V}, I_C=2\text{mA}$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			0. 22	V	$I_C=50\text{mA}, I_B=10\text{mA}$
V_{BE}	Base-Emitter Voltage			1. 0	V	$V_{CE}=5\text{V}, I_C=2\text{mA}$
f_T	Current Gain-Bandwidth Product	150	400		MHz	$V_{CE}=5\text{V}, I_C=10\text{mA}$
C_{ob}	Output Capacitance		3. 5		pF	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$